



DESCRIPTION

The AO2122 is a Dual CMOS operational amplifier use auto-zero techniques to simultaneously provide very low offset voltage (5 μ V Max) and near-zero drift over time and temperature.

This AO2122 of amplifier has ultralow noise, offset and power.

This AO2122 has high-precision operational amplifier offset high input impedance and rail-to-rail input and rail-to-rail output swing. With high gain-bandwidth product of 350KHz and slew rate of 0.17V/ μ s.

Single or dual supplies as low as +2.3V (\pm 1.15V) and up to +5.5V (\pm 2.75V) may be used.

The AO2122 is available in SOP8 and MSOP8, DFN8 (2x2) package.

ORDERING INFORMATION

| Package Type | Part Number | |
|-------------------------------------|---|-------------|
| SOP8 SPQ: 4,000pcs/Reel | M8 | AO2122M8R |
| | | AO2122M8VR |
| MSOP8 SPQ: 4,000pcs/Reel | MS8 | AO2122MS8R |
| | | AO2122MS8VR |
| DFN8 (2x2) SPQ: 3,000pcs/Reel | J8 | AO2122J8R |
| | | AO2122J8VR |
| Note | V: Halogen free Package R: Tape & Reel | |
| AiT provides all RoHS products | | |

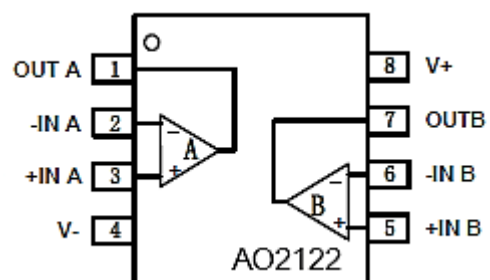
FEATURES

- Low Offset Voltage: 1uV(TYP.)
- Input Offset Drift: \pm 0.005 μ V/ $^{\circ}$ C
- High Gain Bandwidth Product: 350KHz
- Rail-to-Rail Input and Output
- High Gain, CMRR, PSRR:130dB
- High Slew Rate: 0.17V/ μ s
- Low Noise: 3.2uVp-p (0.01~10Hz)
- Low Power Consumption: 60 μ A /op amp
- Overload Recovery Time:6us
- Low Supply Voltage: 2.3 V to 5.5 V
- No External Capacitors Required
- Extended Temperature: -40 $^{\circ}$ C ~ +125 $^{\circ}$ C

APPLICATION

- Temperature Sensors
- Medical/Industrial Instrumentation
- Pressure Sensors
- Battery-Powered Instrumentation
- Active Filtering
- Weight Scale Sensor
- Strain Gage Amplifiers
- Power Converter/Inverter

TYPICAL APPLICATION



**PIN DESCRIPTION**

| | | | | | |
|---|--|--|--|--|--|
| <p>AO2122 SOP8</p> <p>SOP8, M8 Top View</p> | | | <p>AO2122 MSOP8</p> <p>MSOP8, MS8 Top View</p> | | |
| <p>AO2122 DFN8</p> <p>DFN8, J8 Top View</p> | | | | | |

| PIN# | | | Symbol | Function |
|------|-------|---------------|--------|---------------------------------|
| SOP8 | MSOP8 | DFN8 (2x2) | | |
| 1 | 1 | 1 | OUT A | Output A |
| 2 | 2 | 2 | -IN A | Inverting Input A |
| 3 | 3 | 3 | +IN A | Noninverting Input A |
| 4 | 4 | 4 | V- | Negative (lowest) power supply |
| 5 | 5 | 5 | +IN B | Noninverting Input B |
| 6 | 6 | 6 | -IN B | Inverting Input B |
| 7 | 7 | 7 | OUT B | Output B |
| 8 | 8 | 8 | V+ | Positive (highest) power supply |



ABSOLUTE MAXIMUM RATINGS

| | | |
|---|------------------------|--|
| V _S , Supply, V _S =(V ₊) - (V ₋), Voltage | | 7.0V |
| Signal Input Pin, Voltage ⁽¹⁾ | | (V ₋)-0.5 to (V ₊)0.5V |
| Signal Output Pin, Voltage ⁽²⁾ | | (V ₋)-0.5 to (V ₊)0.5V |
| Signal Input Pin, Current ⁽¹⁾ | | ±10mA |
| Signal Output Pin, Current ⁽²⁾ | | ±55mA |
| Output Short-Circuit, Current ⁽³⁾ | | Continuous |
| θ _{JA} , Package Thermal Impedance ⁽⁴⁾ | SOP8 | 110°C/W |
| | MSOP8 | 170°C/W |
| | DFN8(2x2) | 80°C/W |
| T _A , Operating Range | | -40°C ~ +125°C |
| T _{STG} , Storage Temperature | | -65°C ~ +150°C |
| T _J , Junction Temperature ⁽⁵⁾ | | -40°C ~ +150°C |
| ESD Ratings | | |
| V _(ESD) , Electrostatic Discharge | Human-Body Model (HBM) | ±5000V |
| | Machine Model (MM) | ±400V |

*Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

(1) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.

(2) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±55mA or less.

(3) Short-circuit to ground, one amplifier per package.

(4) The package thermal impedance is calculated in accordance with JEDEC-51.

(5) The maximum power dissipation is a function of T_{J (MAX)}, R_{θJA}, and T_A. The maximum allowable power dissipation at any ambient temperature is PD = (T_{J (MAX)} - T_A) / R_{θJA}. All numbers apply for packages soldered directly onto a PCB.

RECOMMENDED OPERATING CONDITIONS

| Parameter | Symbol | Conditions | Min | Typ. | Max | Unit |
|----------------|---|---------------|-------|------|-------|------|
| Supply Voltage | V _S =(V ₊) - (V ₋) | Single-Supply | 2.3 | - | 5.5 | V |
| | | Dual-Supply | ±1.15 | | ±2.75 | |



ELECTRICAL CHARACTERISTICS

At $T_A = +25^\circ\text{C}$, $V_S = 5\text{V}$, $R_L = 10\text{k}\Omega$ connected to $V_S/2$, and $V_{OUT} = V_S/2$, unless otherwise noted.

| Parameter | Symbol | Conditions | Min | Typ. | Max | Unit |
|---|-------------------|--|------|-------------|------------|------------------------------|
| OFFSET VOLTAGE | | | | | | |
| Input Offset Voltage | V_{OS} | $V_{CM} = V_S / 2$ | -5 | ± 1 | 5 | μV |
| Input Offset Voltage Average Drift | $V_{OS} T_C$ | | | ± 0.005 | ± 0.05 | $\mu\text{V}/^\circ\text{C}$ |
| Power-Supply Rejection Ratio | PSRR | $V_S = 2.3\text{V}$ to 5.5V , $V_{CM} = 0$ | 110 | 130 | - | dB |
| Channel Separation | dc | | - | 0.1 | - | $\mu\text{V}/\text{V}$ |
| INPUT BIAS CURRENT | | | | | | |
| Input Bias Current ⁽¹⁾⁽²⁾ | I_B | $V_{CM} = V_S/2$ | - | ± 10 | - | pA |
| Input Offset Current ⁽¹⁾ | I_{OS} | | - | ± 10 | - | pA |
| NOISE PERFORMANCE | | | | | | |
| Input Voltage Noise | $e_{n\text{p-p}}$ | $f = 0.01\text{Hz}$ to 10Hz | - | 3.2 | - | μVpp |
| | | $f = 0.01\text{Hz}$ to 1Hz | - | 0.97 | - | μVpp |
| Input Voltage Noise Density | e_n | $f = 1\text{KHz}$ | - | 140 | - | $\text{nV}/\sqrt{\text{Hz}}$ |
| Input Current Noise Density | i_n | $f = 10\text{Hz}$ | - | 15 | - | $\text{fA}/\sqrt{\text{Hz}}$ |
| INPUT VOLTAGE RANGE | | | | | | |
| Common-Mode Voltage Range | V_{CM} | | -0.1 | - | 0.1 | V |
| Common-Mode Rejection Ratio | CMRR | $(V_-) - 0.1\text{V} < V_{CM} < (V_+) + 0.1\text{V}$ | 110 | 130 | - | dB |
| INPUT CAPACITANCE | | | | | | |
| Differential | | | - | 1 | - | pF |
| Common-Mode | | | - | 5 | - | pF |
| OPEN-LOOP GAIN | | | | | | |
| Open-Loop Voltage Gain | A_{OL} | $R_L = 10\text{k}\Omega$, $V_O = 0.3\text{V} \sim 4.7\text{V}$, $T_A = -40^\circ\text{C} \sim +125^\circ\text{C}$ | 110 | 130 | - | dB |
| DYNAMIC PERFORMANCE | | | | | | |
| Slew Rate ⁽⁵⁾ | SR | $G = +1$ | - | 0.17 | - | $\text{V}/\mu\text{s}$ |
| Gain-Bandwidth Product | GBW | | - | 350 | - | KHz |
| Overload Recovery Time | t_{OR} | | - | 6 | - | μs |
| OUTPUT CHARACTERISTICS | | | | | | |
| Output Voltage High | V_{OH} | $R_L = 100\text{k}\Omega$ to GND | 4.99 | 4.998 | - | V |
| | | $R_L = 10\text{k}\Omega$ to GND | 4.95 | 4.98 | - | V |
| Output Voltage Low | V_{OL} | $R_L = 100\text{k}\Omega$ to V_+ | - | 1 | 10 | mV |
| | | $R_L = 10\text{k}\Omega$ to V_+ | - | 10 | 30 | mV |
| Short-Circuit Current ⁽³⁾⁽⁴⁾ | I_{SC} | | - | 25 | - | mA |
| POWER SUPPLY | | | | | | |
| Operating Voltage Range | V_S | | 2.3 | - | 5.5 | V |
| Quiescent Current/Amplifier | I_Q | | - | 60 | 87 | μA |

(1) This parameter is ensured by design and/or characterization and is not tested in production.

(2) Positive current corresponds to current flowing into the device.

(3) The maximum power dissipation is a function of $T_{J(\text{MAX})}$, $R_{\theta JA}$, and T_A . The maximum allowable power dissipation at any ambient temperature is $PD = (T_{J(\text{MAX})} - T_A) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.

(4) Short circuit test is a momentary test.

(5) Number specified is the slower of positive and negative slew rates.



TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Offset Voltage Production Distribution

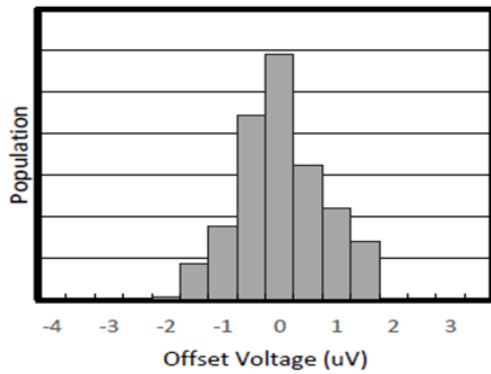


Fig 2. Offset Voltage Production Distribution

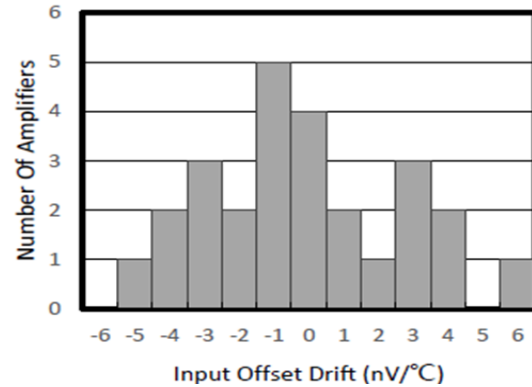


Fig 3. Open-Loop Gain and Phase vs. Frequency

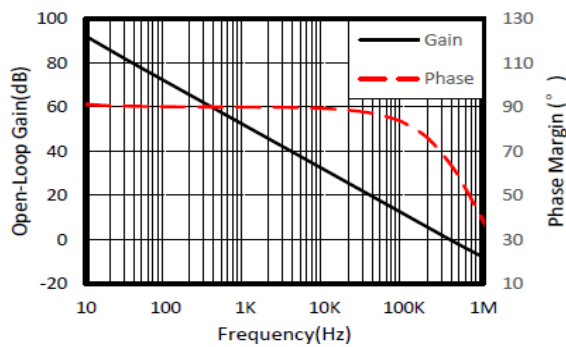


Fig 4. Input Bias Current vs. Temperature

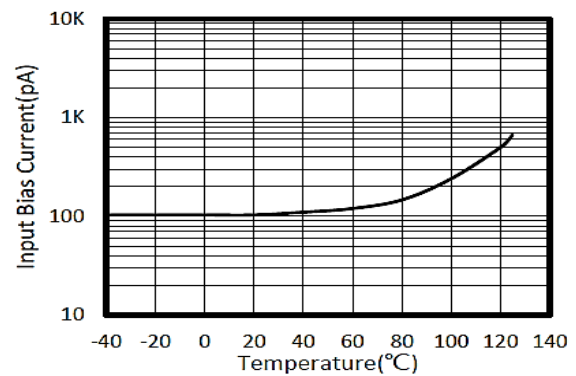


Fig 5. Power-Supply Rejection Ratio vs. Frequency

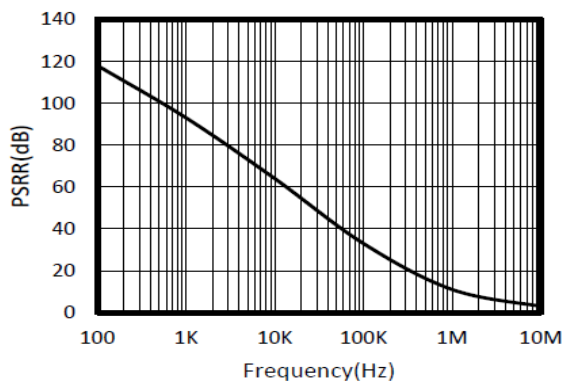


Fig 6. Common-Mode Rejection Ratio vs. Frequency

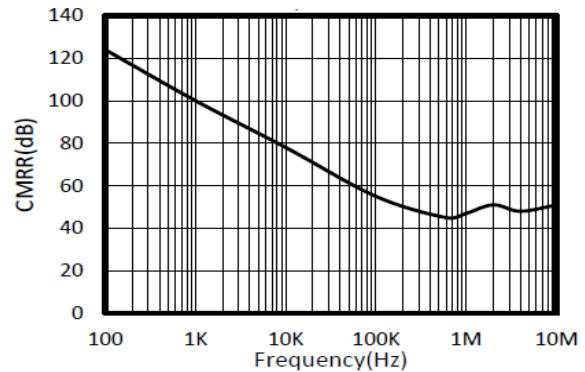




Fig 7. Quiescent Current vs. Temperature

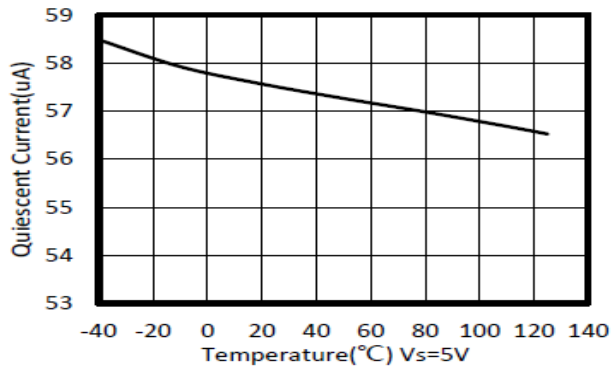


Fig 8. Quiescent Current vs. Temperature

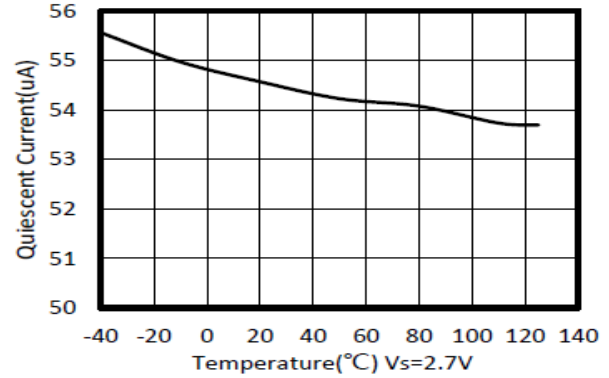


Fig 9. Sink Current vs. Temperature

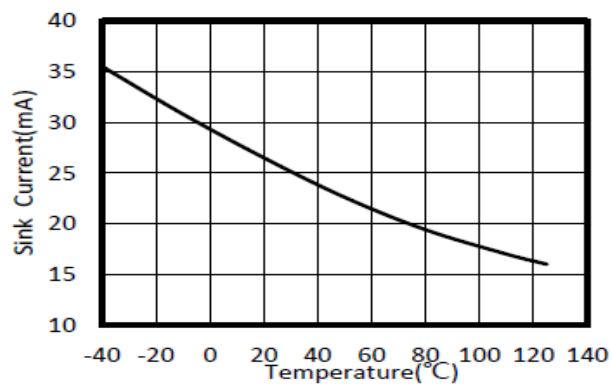


Fig 10. Source Current vs. Temperature

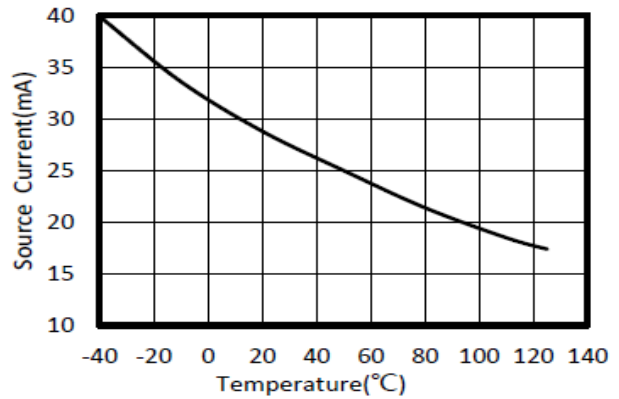


Fig 11. Small-Signal Step Response

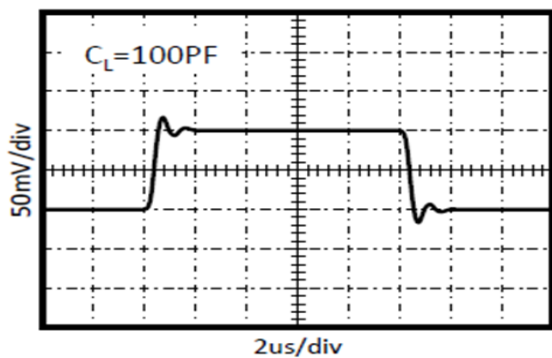


Fig 12. Large-Signal Step Response

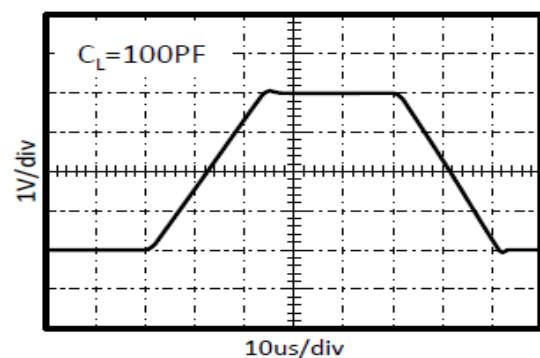




Fig 13. Positive Overvoltage Recovery

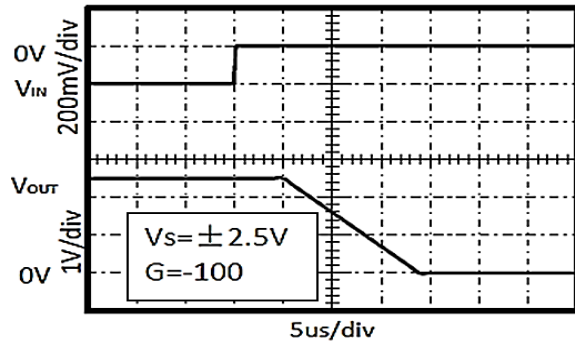


Fig 14. Negative Overvoltage Recovery

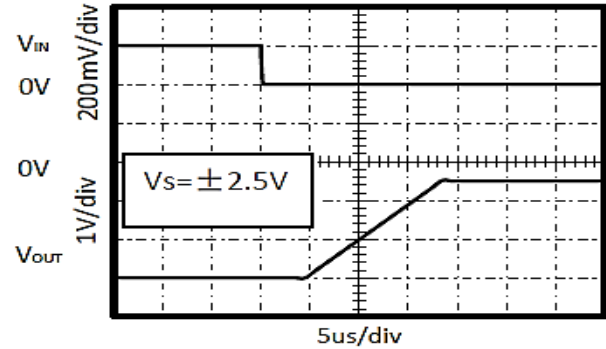


Fig 15. 0.01Hz to 10Hz Noise at $V_S=5V$

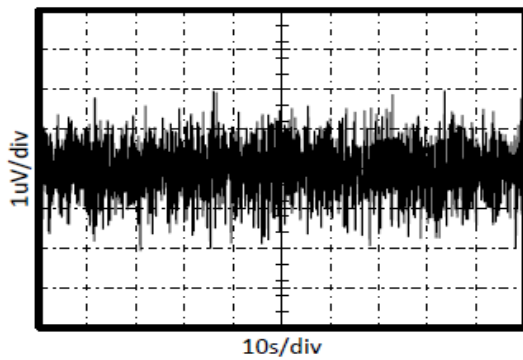


Fig 16. 0.01Hz to 10Hz Noise at $V_S=2.7V$

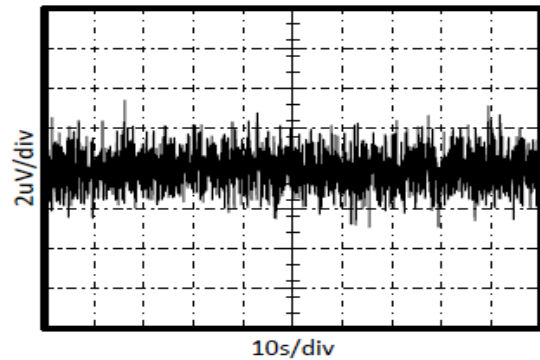


Fig 17. 0.01Hz to 1Hz Noise at $V_S=5V$

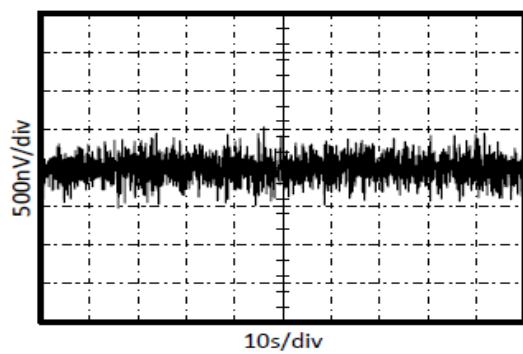
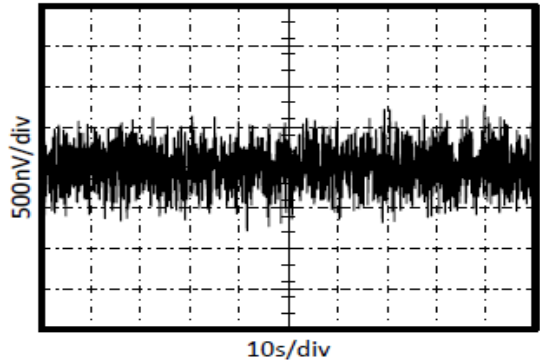
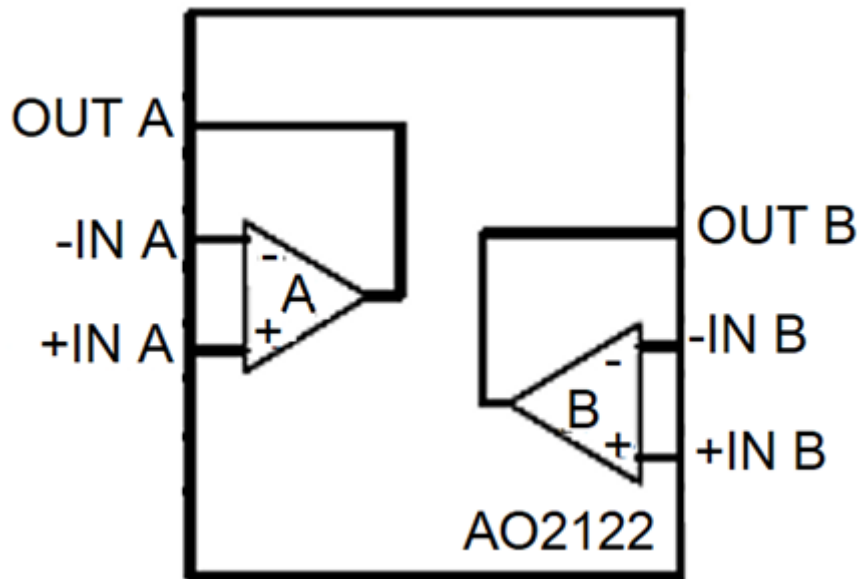


Fig 18. 0.01Hz to 1Hz Noise at $V_S=2.7V$





BLOCK DIAGRAM





DETAILED INFORMATION

Application Notes

The AO2122 is unity-gain stable and free from unexpected output phase reversal op amp. It use auto-zeroing techniques to provide low offset voltage and very low drift over time and temperature. Good layout practice mandates use of a 0.1 μ F capacitor practice mandates use of a 0.1 μ F capacitor placed closely across the supply pins.

For lowest offset voltage and precision performance, circuit layout and mechanical conditions should be optimized. Avoid temperature gradients that create thermoelectric (Seebeck) effects in thermocouple junctions formed from connecting dissimilar conductor. These thermally-generated potentials can be made to cancel by assuring that they are equal on both input terminals.

- Use Low Thermoelectric-Coefficient Connections (avoid dissimilar metals).
- Thermally Isolate Components From Power Supplies or other Heat-Sources
- Shield Op Amp and input Circuitry from Air Currents, such as cooling fans.

Following these guidelines will reduce the likelihood of junctions being at different temperatures, which can cause thermoelectric voltages of 0.1 μ V/ $^{\circ}$ C or higher, depending on materials used.

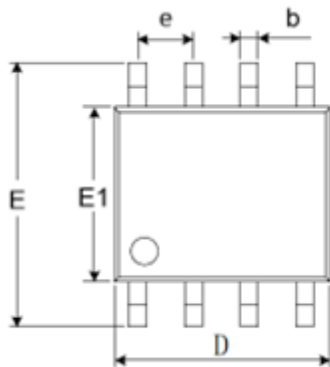
Operating Voltage

The AO2122 operates over a power-supply range of 2.3V to +5.5V (± 1.15 V to ± 2.75 V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier.

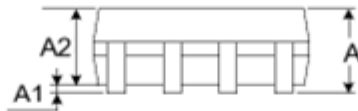


PACKAGE INFORMATION

Dimension in SOP8 (Unit: mm)



TOP VIEW

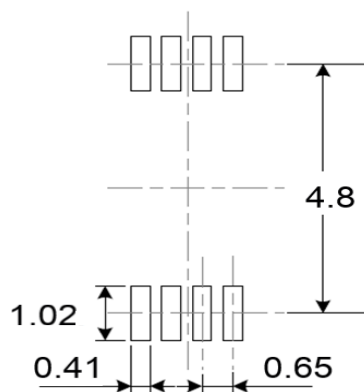


BOTTOM VIEW



SIDE VIEW

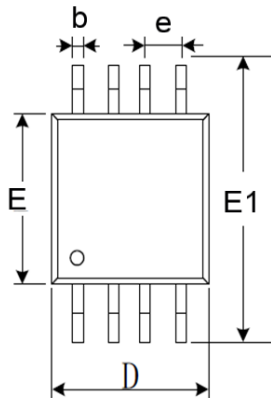
Recommended Land Pattern



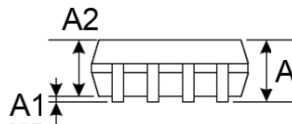
| Symbol | Millimeters | |
|--------|-------------|-------|
| | Min | Max |
| A | 0.820 | 1.100 |
| A1 | 0.020 | 0.150 |
| A2 | 0.750 | 0.950 |
| b | 0.250 | 0.380 |
| c | 0.090 | 0.230 |
| D | 2.900 | 3.100 |
| e | 0.650 BSC | |
| E | 2.900 | 3.100 |
| E1 | 4.750 | 5.050 |
| L | 0.400 | 0.800 |
| θ | 0° | 6° |



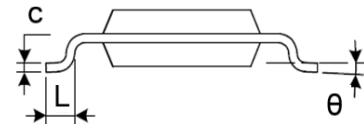
Dimension in MSOP8 (Unit: mm)



TOP VIEW

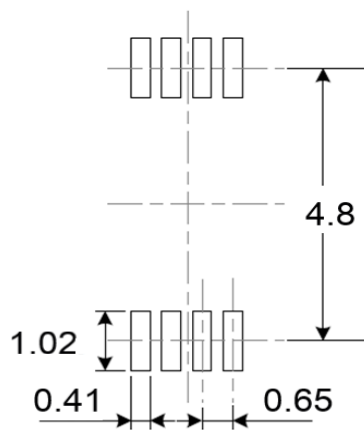


BOTTOM VIEW



SIDE VIEW

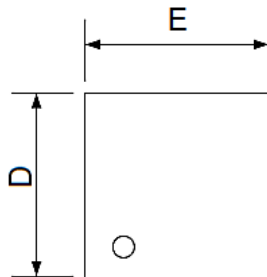
Recommended Land Pattern



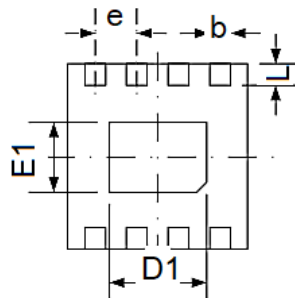
| Symbol | Millimeters | |
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| c | 0.090 | 0.230 |
| D | 2.900 | 3.100 |
| e | 0.650 BSC | |
| E | 2.900 | 3.100 |
| E1 | 4.750 | 5.050 |
| L | 0.400 | 0.800 |
| θ | 0° | 6° |



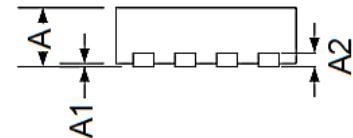
Dimension in DFN8 (2x2) (Unit: mm)



TOP VIEW

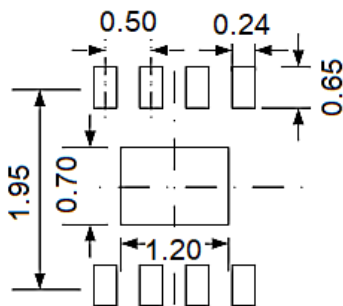


BOTTOM VIEW



SIDE VIEW

Recommended Land Pattern



| Symbol | Millimeters | |
|--------|-------------|-------|
| | Min | Max |
| A | 0.700 | 0.800 |
| A1 | 0.000 | 0.050 |
| A2 | 0.203 TYP. | |
| b | 0.180 | 0.300 |
| D | 1.900 | 2.100 |
| D1 | 1.100 | 1.300 |
| E | 1.900 | 2.100 |
| E1 | 0.600 | 0.800 |
| e | 0.500 TYP. | |
| L | 0.250 | 0.450 |



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